

## Poster Session 4

MAR 9 (Wed), 13:00-14:30

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**Synthesis of Ni-Al Intermetallic Nanoparticle Catalysts by Thermal Plasma**

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**Photoluminescence of ZnNb<sub>2</sub>O<sub>6</sub> Doped with Tm<sup>3+</sup> Nanocrystal**

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**Synthesis of Intermetallic Ni<sub>3</sub>C Nanoparticles by Chemical Reduction at Room Temperature**

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**Synthesis of Dense Phases of Materials Using Plasma Microexplosions Induced by Ultrashort Laser Pulses**

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**Structural Characteristics of Au Nanoparticles Synthesized by Solution Plasma Process**

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